

*B1 end*

etching said metal stack and said layer of resistor material using said first pattern to form a plurality of metal lines in addition to and separate from a thin film resistor area;

removing said first pattern;

forming a second pattern to expose a portion of said metal stack over the thin film resistor area;

removing said exposed portion of said metal stack to form a thin film resistor.

*sub*

*B2*

Amend claim 8 to read as follows:

8. (amended) A method of fabricating a thin film resistor in an integrated circuit, comprising the steps of

providing a semiconductor body having a first interlevel dielectric layer;

forming a layer of resistor material over said first interlevel dielectric layer;

forming a metal stack on said layer of resistor material;

forming a first pattern over said metal stack, said first pattern covering said metal stack where a plurality of metal lines and said thin film resistor are desired;

dry etching said metal stack and said layer of resistor material using said first pattern to form said plurality of metal lines in addition to and separate from said thin film resistor;

removing said first pattern;

forming a second pattern to expose a portion of said metal stack over a thin film resistor area;

removing said exposed portion of said metal stack using a wet etch to form said thin film resistor;

removing said second pattern; and

forming a second interlevel dielectric layer over said plurality of metal lines and said thin film resistor.

Cancel Claims 14-16.